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# NTE573
# Schottky Barrier Rectifier

**Description:**

The NTE573 is an axial lead metal–to–silicon power diode using the Schottky Barrier principle. State–of–the–art geometry features epitaxial construction with oxide passivation and metal overlap contact. This device is ideally suited for use in low–voltage, high–frequency inverters, as free wheeling diodes, and polarity protection diodes.

**Features:**

- Low Forward Voltage
- Low Power Loss
- High Surge Capacity
- Low Stored Charge Majority Carrier Conduction
- High Efficiency
- High Switching Capability

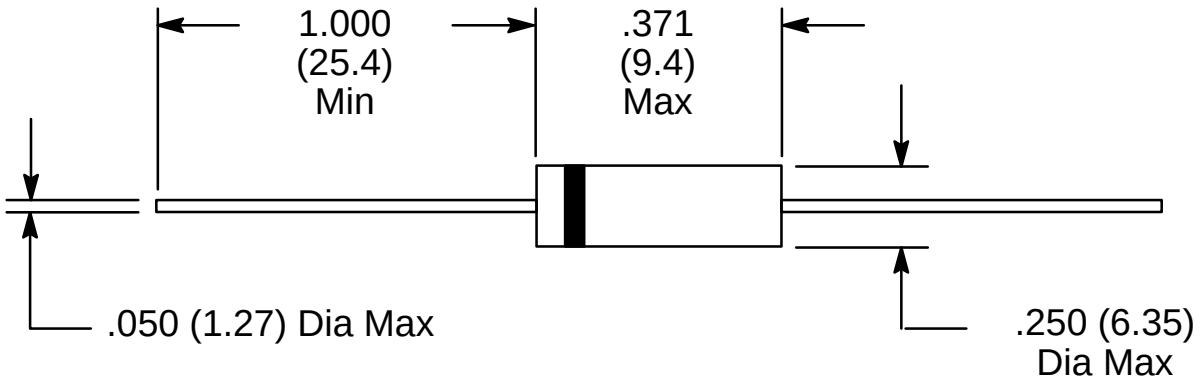
**Absolute Maximum Ratings:**

Peak Repetitive Reverse Voltage, $V_{RRM}$ . . . . . 60V
Working Peak Reverse Voltage, $V_{RWM}$ . . . . . 60V
DC Blocking Voltage, $V_R$ . . . . . 60V
RMS Reverse Voltage, $V_{R(RMS)}$ . . . . . 42V
Average Forward Rectified Current, $I_O$ . . . . . 5A
Non–Repetitive Peak Surge Current, $I_{FSM}$
(Surge applied at rated load conditions half–wave, single phase, 60Hz, $T_L$ = +70°C) . 250A
Operating Junction Temperature Range, $T_J$ . . . . . –65° to +125°C
Storage Temperature Range, $T_{stg}$ . . . . . –65° to +125°C

**Electrical Characteristics:**

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| Instantaneous Forward Voltage | $V_F$ | $I_F$ = 5A | – | – | 0.70 | V |
| | | $I_F$ = 15A | – | – | 0.95 | V |
| Instantaneous Reverse Current | $I_R$ | $V_R$ = 60V, $T_L$ = +25°C | – | – | 5 | mA |
| | | $V_R$ = 60V, $T_L$ = +100°C | – | – | 50 | mA |
| Junction Capacitance | $C_P$ | Note 1 | – | 380 | – | pF |

Note 1. Measured at 1MHz and applied reverse voltage of 4 volts.




Color Band Denotes Cathode